

Description

The 9FGV1004 is a member of IDT's PhiClock™ programmable clock generator family. The 9FGV1004 provides 1 copy each of 2 integer-related frequencies, 2 copies of a fractional or spread-spectrum frequency and two copies of the crystal reference input. Two select pins allow for hardware selection of the desired configuration, or two I²C bits all easy software selection of the desired configuration. The user may configure any one of the four OTP configurations as the default when operating in I²C mode. Four unique I²C addresses are available, allowing easy I²C access to multiple components.

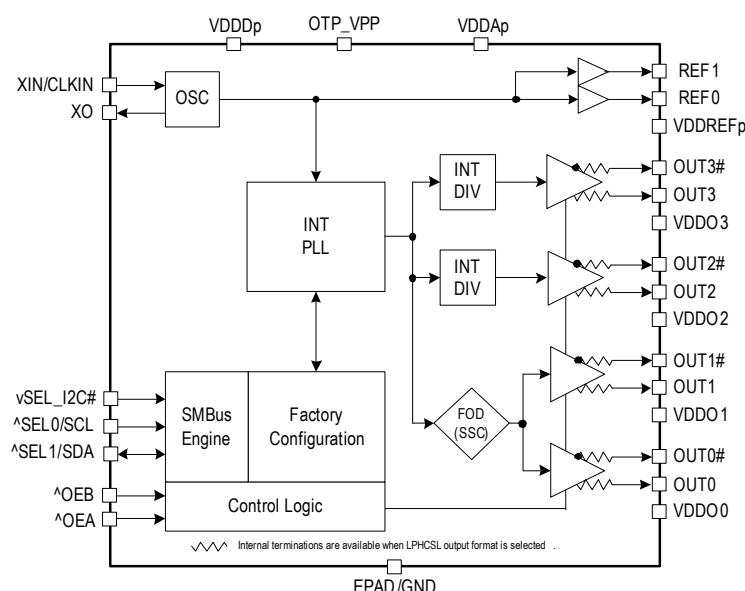
Typical Applications

- HPC
- Storage
- 10G/25G Ethernet
- Fiber Optic Modules
- SSDs

Output Features

- 4 programmable output pairs
- 2 integer output frequencies and 1 fractional or spread spectrum output frequency per configuration
- 2 LVCMOS REF outputs
- 10MHz–325MHz output frequency (LVDS or LP-HCSL), integer configuration
- 10MHz–200MHz output frequency (LVCMOS), integer configuration
- 10MHz–156.25MHz output frequency, fractional or spread spectrum configuration

Block Diagram



Features

- 1.8V to 3.3V core V_{DD} and V_{DDREF}
- Individual 1.8V to 3.3V V_{DDO} for each output pair
- Supports HCSL, LVDS and LVCMOS I/O standards
- Supports LVPECL and CML logic with easy AC coupling – see application note [AN-891](#) for alternate terminations
- HCSL utilizes IDT's LP-HCSL technology for improved performance, lower power and higher integration:
 - Programmable output impedance of 85 or 100Ω
- On-board OTP supports up to 4 complete configurations
- Configuration selected via strapping pins or I²C
- < 125mW at 1.8V, < 230mW at 3.3V with outputs running at 100MHz
- 4 programmable I²C addresses: D0/D1, D2/D3, D4/D5, D6/D7 read/write
- Programmable spread spectrum modulation frequency and amount
- Supported by IDT [Timing Commander™](#) software
- Space saving 4 × 4 mm 24-VFQFPN

Key Specifications

- 331fs rms typical phase jitter (OUT[3:0] outputs) at 156.25MHz (12kHz–20MHz)
- PCIe Gen 1–4 compliant (spread spectrum off)
- PCIe Gen 1–3 compliant (spread spectrum on)

PCIe Clocking Architectures Supported

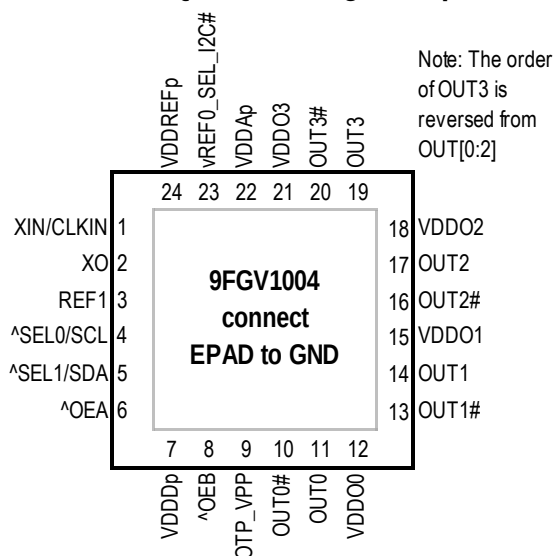
- Common Clocked (CC)
- Independent Reference without spread spectrum (SRnS)

Table 1. OE Mapping

OE[B:A]	OUT0	OUT1	OUT2	OUT3	REF0	REF1
00	Running	Stopped	Running	Stopped	Running	Running
01	Running	Running	Stopped	Stopped	Running	Running
10	Stopped	Stopped	Running	Running	Running	Running
11	Running	Running	Running	Running	Running	Running

Pin Assignments

Figure 1. Pin Assignments for 4 x 4 mm 24-VFQFPN Package – Top View



4 × 4 mm 24-VFQFPN, 0.5mm pitch

^ prefix indicates internal 120kOhm pull-up resistor

v prefix indicates internal 120kOhm pull-down resistor

Pin Descriptions

Table 2. Pin Descriptions

Number	Name	Type	Description
1	XIN/CLKIN	Input	Crystal input or reference clock input.
2	XO	Output	Crystal output.
3	REF1	Output	LVC MOS reference output.
4	^SEL0/SCL	Input	Select pin for internal frequency configurations/I ² C clock pin. Function is determined by state of SEL_I2C# upon power-up. This pin has an internal pull-up.
5	^SEL1/SDA	I/O	Select pin for internal frequency configurations/I ² C data pin. Function is determined by state of SEL_I2C# upon power-up. This pin has an internal pull-up.
6	^OEA	Input	Active high input for enabling outputs. This pin has an internal pull-up resistor. 0 = disable outputs, 1 = enable outputs.

Table 2. Pin Descriptions (Cont.)

Number	Name	Type	Description
7	VDDDp	Power	Digital power. 1.8V to 3.3V. VDDAp and VDDDp should be connected to the same power supply.
8	^OEB	Input	Active high input for enabling outputs. This pin has an internal pull-up resistor. 0 = disable outputs, 1 = enable outputs.
9	OTP_VPP	Power	Voltage for programming OTP. During normal operation, this pin should be connected to the same power rail as V _{DD} .
10	OUT0#	Output	Complementary output clock 0.
11	OUT0	Output	Output clock 0.
12	VDDO0	Power	Power supply for output 0.
13	OUT1#	Output	Complementary output clock 1.
14	OUT1	Output	Output clock 1.
15	VDDO1	Power	Power supply for output 1.
16	OUT2#	Output	Complementary output clock 2.
17	OUT2	Output	Output clock 2.
18	VDDO2	Power	Power supply for output 2.
19	OUT3	Output	Output clock 3.
20	OUT3#	Output	Complementary output clock 3.
21	VDDO3	Power	Power supply for output 3.
22	VDDAp	Power	Power supply for analog circuits. VDDAp and VDDDp should be connected to the same power supply. Programmable for nominally voltages of 1.8V, 2.5V or 3.3V.
23	vREF0_SEL_I2C#	Latched I/O	Latched input/LVCMOS output. At power-up, the state of this pin is latched to select the state of the I ² C pins. After power-up, the pin acts as an LVCMOS reference output. This pin has an internal pull-down. 1 = SEL0/SEL1. 0 = SCL/SDA.
24	VDDREFp	Power	Power supply for REF0 and REF1 and the internal XO. Programmable to 1.8V, 2.5V or 3.3V.
25	EPAD	GND	Connect to ground.

Note: Unused outputs can be programmed off and left floating. V_{DDREF} and V_{DDO0} have to be connected.

Absolute Maximum Ratings

The absolute maximum ratings are stress ratings only. Stresses greater than those listed below can cause permanent damage to the device. Functional operation of the 9FGV1004 at absolute maximum ratings is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Table 3. Absolute Maximum Ratings

Parameter	Rating
Supply Voltage, V_{DDA} , V_{DDD} , V_{DDO}	3.465V
Storage Temperature, T_{STG}	-65°C to 150°C
ESD Human Body Model	2000V
Junction Temperature	125°C
Inputs	
XIN/CLKIN	0V to 1.2V voltage swing
Other Inputs	-0.5V to V_{DDD}
Outputs	
Outputs, V_{DDO} (LVCMOS)	-0.5V to $V_{DDO} + 0.5V$
Outputs, IO (SDA)	10mA

Thermal Characteristics

Table 4. Thermal Characteristics

Parameter	Symbol	Conditions	Package	Typical Values	Units	Notes
Thermal Resistance (devices with external crystal)	θ_{JC}	Junction to case	NBG24	52	°C/W	1
	θ_{Jb}	Junction to base		2.3	°C/W	1
	θ_{JA0}	Junction to air, still air		44	°C/W	1
	θ_{JA1}	Junction to air, 1 m/s air flow		37	°C/W	1
	θ_{JA3}	Junction to air, 3 m/s air flow		33	°C/W	1
	θ_{JA5}	Junction to air, 5 m/s air flow		32	°C/W	1

¹ EPAD soldered to board.

Recommended Operating Conditions

Table 5. Recommended Operating Conditions

Symbol	Parameter	Minimum	Typical	Maximum	Units
V_{DDOX}	Power supply voltage for supporting 1.8V outputs.	1.71	1.8	1.89	V
	Power supply voltage for supporting 2.5V outputs.	2.375	2.5	2.625	V
	Power supply voltage for supporting 3.3V outputs.	3.135	3.3	3.465	V
V_{DDD}	Power supply voltage for core logic functions.	1.71		3.465	V
V_{DDA}	Analog power supply voltage. Use filtered analog power supply if available.	1.71		3.465	V
T_A	Operating temperature, ambient.	-40		85	°C
C_L	Maximum load capacitance (3.3V LVCMOS only).			15	pF
t_{PU}	Power up time for all V_{DDs} to reach minimum specified voltage (power ramps must be monotonic).	0.05		5	ms

Electrical Characteristics

$V_{DDx} = 3.3V \pm 5\%$, $2.5V \pm 5\%$, $1.8V \pm 5\%$, $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$ unless stated otherwise.

Table 6. Common Electrical Characteristics

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units	Notes
Input Frequency	f_{IN}	Crystal input frequency.	8	25	50	MHz	1
		CLKIN input frequency.	1		240	MHz	5
Output Frequency	f_{OUT}	Differential clock output (LVDS/LP-HCSL).	10		325	MHz	
		Single-ended clock output (LVCMOS).	10		200	MHz	
		Fractional or spread spectrum configuration.	10		156.25	MHz	
VCO Frequency	f_{VCO}	VCO operating frequency range.	2400	2500	2600	MHz	
Loop Bandwidth	f_{BW}	Input frequency = 25MHz.	0.06		0.9	MHz	
Input High Voltage	V_{IH}	SEL[1:0].	$0.7 \times V_{DDD}$		$V_{DDD} + 0.3$	V	
Input Low Voltage	V_{IL}	SEL[1:0].	GND - 0.3		0.8	V	
Input High Voltage	V_{IH}	REF/SEL_I2C#.	$0.65 \times V_{DDREF}$		$V_{DDREF} + 0.3$	V	
Input Low Voltage	V_{IL}	REF/SEL_I2C#.	-0.3		0.4	V	
Input High Voltage	V_{IH}	XIN/CLKIN.	0.8		1.2	V	
Input Low Voltage	V_{IL}	XIN/CLKIN.	-0.3		0.4	V	
Input Rise/Fall Time	T_R/T_F	SEL1/SDA, SEL0/SCL.			300	ns	
Input Capacitance	C_{IN}	SEL[1:0].		3	7	pF	
Internal Pull-up Resistor	R_{UP}	SEL[1:0] at 25°C.	200	237	300	kΩ	

Table 6. Common Electrical Characteristics (Cont.)

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units	Notes
Internal Pull-down Resistor	R _{DOWN}	REF/SEL_I2C#.	200	237	300	kΩ	
Programmable capacitance at XIN and XO (XIN in parallel with XO)	C _L	XIN/CLKIN, XO.	0		8	pF	
Input Duty Cycle	t2	CLKIN, measured at V _{DDREF} /2.	40	50	60	%	
Output Duty Cycle	t3	LVC MOS, f _{OUT} > 156.25MHz.	40	50	60	%	
		LVC MOS, f _{OUT} ≤ 156.25MHz.	45	50	55	%	
		LVDS, LP-HCSL outputs.	45	49.9	55	%	
Clock Jitter	t6	Cycle-to-cycle jitter (Peak-to-Peak), See "Test Frequencies for Jitter Measurements in Common Electrical Characteristics" for configurations.		27		ps	4
		Reference clock RMS phase jitter (12kHz to 5MHz integration range). See "Test Frequencies for Jitter Measurements in Common Electrical Characteristics" for configurations.		250		fs rms	4
		OUTx RMS phase jitter(12kHz to 20MHz integration range) differential output. See "Test Frequencies for Jitter Measurements in Common Electrical Characteristics" for configurations.		320		fs rms	4
Output Skew	t7	Skew between the same frequencies, with outputs using the same driver format.		34		ps	
Lock Time	t8	PLL lock time from V _{DDs} reaching 1.5V.		5	10	ms	2, 3

¹ Practical lower frequency is determined by loop filter settings.

² Includes loading the configuration bits from OTP to registers.

³ Actual PLL lock time depends on the loop configuration.

⁴ Actual jitter is configuration dependent. These values are representative of what the device can achieve.

⁵ Input doubler off. Maximum input frequency with input doubler on is 160MHz.

Table 7. Test Frequencies for Jitter Measurements in Common Electrical Characteristics

Device	XIN/CLKIN	OUT0	OUT1	OUT2	OUT3	Unit	Notes
9FGV1004	25	100		125.00	156.25	MHZ	2,3

¹ Measurement with spread spectrum off.

² All outputs measured with 100MHz outputs both spreading and non-spreading.

³ All jitter measurements are made with OUTx outputs configured as LVDS or LP-HCSL and REF output on unless noted.

Table 8. LVCMOS Output Electrical Characteristics

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units	Notes
Slew Rate	S_R	3.3V $\pm$ 5%, 20% to 80% of V_{DDO} (output load = 4.7pF).	2.5	3.7	4.6	V/ns	
		2.5V $\pm$ 5%, 20% to 80% of V_{DDO} (output load = 4.7pF).	1.5	2.4	4.6	V/ns	
		1.8V $\pm$ 5%, 20% to 80% of V_{DDO} (output load = 4.7pF).	0.8	1.7	3.5	V/ns	
Output High Voltage	V_{OH}	I_{OH} = -15mA at 3.3V. I_{OH} = -12mA at 2.5V. I_{OH} = -8mA at 1.8V.	$0.8 \times V_{DDO}$		V_{DDO}	V	
Output Low Voltage	V_{OL}	I_{OL} = 15mA at 3.3V. I_{OL} = 12mA at 2.5V. I_{OL} = 8mA at 1.8V.		0.22	0.4	V	
Output Leakage Current	I_{OZDD}	Programmable outputs, tri-state outputs, V_{DDO} = 3.465V.		0	5	μ A	
		REF outputs, tri-state outputs, V_{DDREF} = 3.465V.		0	5	μ A	
CMOS Output Driver Impedance	R_{OUT}	T_A = 25°C.		17		Ω	

Table 9. LVDS Output Electrical Characteristics

Parameter	Symbol	Minimum	Typical	Maximum	Units	Notes
Differential Output Voltage for the TRUE Binary State	$V_{OT}(+)$	247	328	454	mV	
Differential Output Voltage for the FALSE Binary State	$V_{OT}(-)$	-454	-332	-247	mV	
Change in V_{OT} between Complementary Output States	ΔV_{OT}			50	mV	
Output Common Mode Voltage (Offset Voltage) at 3.3V +5% & 2.5V +5%	V_{OS}	1.125	1.19	1.55	V	
Output Common Mode Voltage (Offset Voltage) at 1.8V +5%	V_{OS}	0.8	0.86	0.95	V	
Change in V_{OS} between Complementary Output States	ΔV_{OS}		0	50	mV	
Outputs Short Circuit Current, V_{OUT+} or V_{OUT-} = 0V or V_{DD}	I_{OS}		6	12	mA	
Differential Outputs Short Circuit Current, $V_{OUT+} = V_{OUT-}$	I_{OSD}		3	12	mA	
Rise Times Tested at 20% – 80%	T_R		257	400	ps	
Fall Times Tested at 80% – 20%	T_F		287	400	ps	

Table 10. Low-Power (LP) Push-Pull HCSL Differential Outputs

$V_{DDO} = 3.3V \pm 5\%$, $2.5V \pm 5\%$, $1.8V \pm 5\%$, $T_A = -40^\circ C$ to $+85^\circ C$ unless stated otherwise.

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units	Notes
Slew Rate	$T_{R/F}$	Scope averaging on.	1	2.5	4	V/ns	2,3,16
Slew Rate Matching	$\Delta T_{R/F}$			9	20	%	1,14,16
Crossing Voltage (abs)	V_{CROSS}	Scope averaging off.	250	424	550	mV	1,4,5,16
Crossing Voltage (var)	ΔV_{CROSS}	Scope averaging off.		16	140	mV	1,4,9,16
Average Clock Period Accuracy	T_{PERIOD_AVG}	Outputs set to 100MHz for PCIe applications.	-100	0	+2600	ppm	2,10,12,13
Absolute Period	T_{PERIOD_ABS}	Includes jitter and spread modulation.	9.949	10	10.101	ns	2,6
Absolute Maximum Voltage	V_{MAX}	Includes 300mV of overshoot (V_{ovs}).	660	808	1150	mV	1,7,15
Absolute Minimum Voltage	V_{MIN}	Includes -300mV of undershoot (V_{uds}).	-300	-54	150	mV	1,8,15

¹ Measured from single-ended waveform.

² Measured from differential waveform.

³ Measured from -150mV to +150mV on the differential waveform (derived from REFCLK+ minus REFCLK-). The signal must be monotonic through the measurement region for rise and fall time. The 300mV measurement window is centered on the differential zero crossing.

⁴ Measured at crossing point where the instantaneous voltage value of the rising edge of REFCLK+ equals the falling edge of REFCLK-.

⁵ Refers to the total variation from the lowest crossing point to the highest, regardless of which edge is crossing. Refers to all crossing points for this measurement.

⁶ Defines as the absolute minimum or maximum instantaneous period. This includes cycle-to-cycle jitter, relative ppm tolerance, and spread spectrum modulation.

⁷ Defined as the maximum instantaneous voltage including overshoot.

⁸ Defined as the minimum instantaneous voltage including undershoot.

⁹ Defined as the total variation of all crossing voltages of rising REFCLK+ and falling REFCLK-. This is the maximum allowed variance in V_{CROSS} for any particular system.

¹⁰ Refer to Section 8.6 of the PCI Express Base Specification, Revision 4.0 for information regarding PPM considerations.

¹¹ System board compliance measurements must use the test load. REFCLK+ and REFCLK- are to be measured at the load capacitors C_L . Single-ended probes must be used for measurements requiring single-ended measurements. Either single-ended probes with math or differential probe can be used for differential measurements. Test load $C_L = 2pF$.

¹² PCIe Gen1 through Gen4 specify $\pm 300ppm$ frequency tolerances. The PhiClock devices already meet the tighter $\pm 100ppm$ frequency tolerances proposed for PCIe Gen5 and required by most servers.

¹³ "ppm" refers to parts per million and is a DC absolute period accuracy specification. 1ppm is 1/1,000,000th of 100.000000MHz exactly or 100Hz. For 100ppm, then we have an error budget of $100Hz/ppm \times 100ppm = 10kHz$. The period is to be measured with a frequency counter with measurement window set to 100ms or greater. The $\pm 100ppm$ applies to systems that do not employ Spread Spectrum Clocking, or that use common clock source. For systems employing Spread Spectrum Clocking, there is an additional 2,500ppm nominal shift in maximum period resulting from the 0.5% down spread resulting in a maximum average period specification of +2,600ppm for Common Clock Architectures. Separate Reference Clock Architectures may have a lower allowed spread percentage.

¹⁴ Matching applies to rising edge rate for REFCLK+ and falling edge rate for REFCLK-. It is measured using a $\pm 75mV$ window centered on the median cross point where REFCLK+ rising meets REFCLK- falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations. The rise edge rate of REFCLK+ should be compared to the fall edge rate of REFCLK-; the maximum allowed difference should not exceed 20% of the slowest edge rate.

¹⁵ At default amplitude settings.

¹⁶ Guaranteed by design and characterization.

Table 11. Filtered Phase Jitter Parameters – PCIe Common Clocked (CC) Architectures

T_{AMB} = over the specified operating range. Supply Voltages per normal operation conditions; see Test Loads for loading conditions.

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Industry Limits	Units	Notes
PCIe Phase Jitter	t _{jphPCIeG1-CC}	PCIe Gen1.		19	47	86	ps (p-p)	1, 2, 3
	t _{jphPCIeG2-CC}	PCIe Gen2 Low Band 10kHz < f < 1.5MHz (PLL BW of 5–16MHz, 8–16MHz, CDR = 5MHz).		0.4	1.3	3	ps (rms)	1, 2
		PCIe Gen2 High Band 1.5MHz < f < Nyquist (50MHz) (PLL BW of 5–16MHz, 8–16MHz, CDR = 5MHz).		1.6	2.7	3.1	ps (rms)	1, 2
	t _{jphPCIeG3-CC}	PCIe Gen3 (PLL BW of 2–4MHz, 2–5MHz, CDR = 10MHz).		0.4	0.64	1	ps (rms)	1, 2
	t _{jphPCIeG4-CC}	PCIe Gen4 (SSC off) (PLL BW of 2–4MHz, 2–5MHz, CDR = 10MHz).		0.35	0.44	0.5	ps (rms)	1, 2

Table 12. Filtered Phase Jitter Parameters – PCIe Independent Reference (IR) Architectures

T_{AMB} = over the specified operating range. Supply Voltages per normal operation conditions; see Test Loads for loading conditions.

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Industry Limits	Units	Notes
PCIe Phase Jitter	t _{jphPCIeG2-SRnS}	PCIe Gen2 (SSC off) (PLL BW of 16MHz, CDR = 5MHz).		1.2	1.5	2	ps (rms)	1, 2, 4, 5
	t _{jphPCIeG3-SRnS}	PCIe Gen3 (SSC off) (PLL BW of 2–4MHz, CDR = 10MHz).		0.4	0.44	0.7	ps (rms)	1, 2, 4, 5

Notes for all PCIe Filtered Phase Jitter tables:

- ¹ Applies to all differential outputs, guaranteed by design and characterization.
- ² Based on PCIe Base Specification Rev4.0 version 0.7draft. See <http://www.pcisig.com> for latest specifications.
- ³ Sample size of at least 100K cycles. This figure extrapolates to 108ps pk-pk at 1M cycles for a BER of 1⁻¹².
- ⁴ IR is the new name for Separate Reference Independent Spread (SRIS) and Separate Reference no Spread (SRNS) PCIe clock architectures.
- ⁵ According to the PCIe Base Specification Rev4.0 version 0.7 draft, the jitter transfer functions and corresponding jitter limits are not defined for the IR clock architecture. Widely accepted *industry* limits using widely accepted *industry* filters are used to populate this table. There are no accepted filters or limits for IR clock architectures at PCIe Gen1 or Gen4 data rates.

Table 13. Current Consumption
 $V_{DDO} = 3.3V \pm 5\%, 2.5V \pm 5\%, 1.8V \pm 5\%$, $T_A = -40^\circ C$ to $+85^\circ C$ unless stated otherwise.

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units	Notes
V_{DDREF} Supply Current	I_{DDREF}	25MHz REFCLK.		4	6	mA	
Core Supply Current	I_{DDCORE}	2500MHz VCO, 25MHz REFCLK.		30	38	mA	3
Output Buffer Supply Current (V_{DDO0})	I_{DDOx}	LVDS, 325MHz.		16	19	mA	2
		LP-HCSL, 100MHz.		16	17	mA	2
		LVC MOS, 50MHz.		13	16	mA	1, 2
		LVC MOS, 200MHz.		21	31	mA	1, 2
Output Buffer Supply Current (V_{DDO1})	I_{DDOx}	LVDS, 325MHz, SSC Off.		8	10	mA	2
		LP-HCSL, 100MHz, SSC Off.		6	8	mA	2
		LP-HCSL, 100MHz, SSC On.		14	17	mA	2
		LVC MOS, 50MHz, SSC Off.		5	6	mA	1, 2
		LVC MOS, 50MHz, SSC On.		9	11	mA	1, 2
		LVC MOS, 200MHz, SSC Off.		13	22	mA	1, 2
Output Buffer Supply Current (V_{DDO2} , V_{DDO3} – per output)	I_{DDOx}	LVDS, 325MHz.		18	22	mA	2
		LP-HCSL, 100MHz.		16	19	mA	2
		LVC MOS, 50MHz.		14	17	mA	1, 2
		LVC MOS, 200MHz.		21	32	mA	1, 2
Total Power Down Current	I_{DDPD}	Programmable outputs in HCSL mode, B37[0] = 0.		20	24	mA	1, 2
		Programmable outputs in LVDS mode, B37[0] = 0.		31	39	mA	1, 2
		Programmable outputs in LVC MOS1 mode, B37[0] = 0.		16	18	mA	1, 2
		Programmable outputs in HCSL mode, B37[6,0] = 0.		10	14	mA	1, 2
		Programmable outputs in LVDS mode, B37[6,0] = 0.		18	29	mA	1, 2
		Programmable outputs in LVC MOS1 mode, B37[6,0] = 0.		6	8	mA	1, 2

¹ Single CMOS driver active for each output pair.

² See Test Loads for details; maximum frequency for SSC outputs is 156.25MHz.

³ $I_{DDCORE} = I_{DDA} + I_{DDD}$.

Table 14. Spread Spectrum Generation Specifications

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Output Frequency	f_{OUT}	Output frequency range of spread spectrum outputs.	10		156.25	MHz
Mod Frequency	f_{MOD}	Modulation frequency.	30 to 60			kHz
Spread%	SSC%	Amount of spread value (programmable) – down spread.	-0.1 to -3.0			%
Spread%	SSC%	Amount of spread value (programmable) – center spread.	± 0.05 to ± 1.5			%

I²C Bus Characteristics

Table 15. I²C Bus DC Characteristics

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Input High Level	V_{IH}	—	$0.7 \times V_{DDD}$			V
Input Low Level	V_{IL}	—			$0.3 \times V_{DDD}$	V
Hysteresis of Inputs	V_{HYS}	—	$0.05 \times V_{DDD}$			V
Input Leakage Current	I_{IN}	—	-1		30	μA
Output Low Voltage	V_{OL}	$I_{OL} = 3mA$.			0.4	V

Table 16. I²C Bus AC Characteristics

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Serial Clock Frequency (SCL)	F_{SCLK}	—	10		400	kHz
Bus free time between STOP and START	t_{BUF}	—	1.3			μs
Setup Time, START	$t_{SU:START}$	—	0.6			μs
Hold Time, START	$t_{HD:START}$	—	0.6			μs
Setup Time, Data Input (SDA)	$t_{SU:DATA}$	—	0.1			μs
Hold Time, Data Input (SDA) ¹	$t_{HD:DATA}$	—	0			μs
Output Data Valid from Clock	t_{OVD}	—			0.9	μs
Capacitive Load for Each Bus Line	C_B	—			400	pF
Rise Time, Data and Clock (SDA, SCL)	t_R	—	$20 + 0.1 \times C_B$		300	ns
Fall Time, Data and Clock (SDA, SCL)	t_F	—	$20 + 0.1 \times C_B$		300	ns
High Time, Clock (SCL)	t_{HIGH}	—	0.6			μs
Low Time, Clock (SCL)	t_{LOW}	—	1.3			μs
Setup Time, STOP	$t_{SU:STOP}$	—	0.6			μs

¹ A device must internally provide a hold time of at least 300ns for the SDA signal (referred to the $V_{IH(MIN)}$ of the SCL signal) to bridge the undefined region of the falling edge of SCL.

Crystal Characteristics

Table 17. Recommended Crystal Characteristics

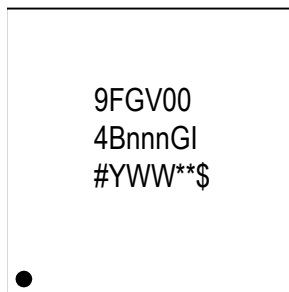
Parameter	Value	Units
Frequency	8 – 50	MHz
Resonance Mode	Fundamental	—
Frequency Tolerance at 25°C	±20	ppm maximum
Frequency Stability, REF at 25°C Over Operating Temperature Range	±20	ppm maximum
Temperature Range (commercial)	0 – 70	°C
Temperature Range (industrial)	-40 – 85	°C
Equivalent Series Resistance (ESR)	50	Ω maximum
Shunt Capacitance (C_0)	7	pF maximum
Load Capacitance (C_L)	8	pF maximum
Drive Level	0.1	mW maximum
Aging per year	±5	ppm maximum

Package Drawings

The package outline drawings are appended at the end of this document and are also accessible from the link below. The package information is the most current data available and is subject to change without notice or revision of this document.

www.idt.com/document/psc/24-vfqfn-package-outline-drawing-40-x-40-x-075-mm-body-05mm-pitch-epad-26-x-26-mm-nbnbg24p2

Marking Diagram



- Lines 1 and 2 are the truncated part number.
- “#” denotes the stepping number.
- “YWW” denotes the last digits of the year and week the part was assembled.
- “**” denotes the lot sequence.
- “\$” denotes the mark code.

Ordering Information

Orderable Part Number	Package	Carrier Type	Temperature
9FGV1004BnnnNBGI	4 × 4 mm, 0.5mm pitch 24-QFN	Trays	-40 to +85°C
9FGV1004BnnnNBGI8	4 × 4 mm, 0.5mm pitch 24-QFN	Tape and Reel	-40 to +85°C

“G” indicates RoHS 6.6 compliance.

“nnn” are decimal digits indicating a specific configuration.

Revision History

Revision Date	Description of Change
December 18, 2018	Updated the Low-Power (LP) Push-Pull HCSL Differential Outputs table and associated notes.
May 30, 2018	Removed “Programmable output amplitude...” bullet.
February 6, 2018	Updated pin 23 description.
January 31, 2018	▪ Updated drive level parameter in <i>Crystal Characteristics</i> table. ▪ Updated <i>Package Outline Drawings</i> text and added hyperlink to document.
August 29, 2017	▪ Initial release.

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Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,
Koto-ku, Tokyo 135-0061, Japan
www.renesas.com

Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit:
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